

Vishay General Semiconductor

Dual Common-Cathode High Voltage Schottky Rectifier



| PRIMARY CHARACTERISTICS | | | | |
|-------------------------|-------------|--|--|--|
| I _{F(AV)} | 2 x 5.0 A | | | |
| V_{RRM} | 90 V, 100 V | | | |
| I _{FSM} | 120 A | | | |
| V _F | 0.75 V | | | |
| T _J max. | 150 °C | | | |

FEATURES





· Low forward voltage drop

High forward surge capability

• High frequency operation

 Solder bath temperature 275 °C maximum, 10 s, per JESD 22-B106

 Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

TYPICAL APPLICATIONS

For use in high frequency rectifier of switching mode power supplies, freewheeling diodes, dc-to-dc converters or polarity protection application.

MECHANICAL DATA

Case: ITO-220AB

Molding compound meets UL 94 V-0 flammability

rating

Base P/N-E3 - RoHS compliant, commercial grade **Terminals:** Matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

| MAXIMUM RATINGS (T _C = 25 °C unless otherwise noted) | | | | | | |
|---|-----------------------------------|----------------------|-------------|------|--|--|
| PARAMETER | SYMBOL | MBRF1090CT | MBRF10100CT | UNIT | | |
| Maximum repetitive peak reverse voltage | V _{RRM} | 90 | 100 | V | | |
| Working peak reverse voltage | V _{RWM} | 90 | 100 | V | | |
| Maximum DC blocking voltage | V _{DC} | 90 | 100 | V | | |
| Maximum average forward rectified current at T _C = 105 °C total dev per diode | [F(A) () | 10 5.0 | | Α | | |
| Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode | I _{FSM} | 120 | | А | | |
| Non-repetitive avalanche energy at $T_J = 25$ °C, $L = 60$ mH per diode | E _{AS} | 60 | | mJ | | |
| Peak repetitive reverse current at t_p = 2 μ s, 1 kHz, T_J = 38 °C \pm 2 °C per diode | I _{RRM} | I _{RRM} 0.5 | | А | | |
| Voltage rate of change (rated V _R) | dV/dt | 10 000 | | V/µs | | |
| Operating junction and storage temperature range | T _J , T _{STG} | - 65 to + 150 | | °C | | |
| Isolation voltage from terminal to heatsink with t = 1 min | V _{AC} | 1500 | | V | | |

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| ELECTRICAL CHARACTERISTICS (T _C = 25 °C unless otherwise noted) | | | | | | |
|---|--|---|--------------------------|--------------|-------------|----------|
| PARAMETER | TEST CC | ONDITIONS | SYMBOL MBRF1090CT MBRF10 | | MBRF10100CT | UNIT |
| Maximum instantaneous forward voltage per diode ⁽¹⁾ | I _F = 5.0 A I _F = 5.0 A | $T_C = 125 ^{\circ}C$ $T_C = 25 ^{\circ}C$ | V _F | 0.75 0.85 | | ٧ |
| Maximum reverse current per diode at working peak reverse voltage (2) | | $T_J = 25 ^{\circ}\text{C}$ $T_J = 100 ^{\circ}\text{C}$ | I _R | 100 6.0 | | μA mA |

Notes

⁽²⁾ Pulse test: Pulse width ≤ 40 ms

| THERMAL CHARACTERISTICS (T _C = 25 °C unless otherwise noted) | | | | | | |
|---|----------------|------------------------|--|------|--|--|
| PARAMETER | SYMBOL | MBRF1090CT MBRF10100CT | | UNIT | | |
| Typical thermal resistance per diode | $R_{	heta JC}$ | 6.8 | | °C/W | | |

| ORDERING INFORMATION (Example) | | | | | | | |
|--------------------------------|-------------------|-----------------|--------------|---------------|---------------|--|--|
| PACKAGE | PREFERRED P/N | UNIT WEIGHT (g) | PACKAGE CODE | BASE QUANTITY | DELIVERY MODE | | |
| ITO-220AB | MBRF10100CT-E3/4W | 1.75 | 4W | 50/tube | Tube | | |

RATINGS AND CHARACTERISTICS CURVES

(T_A = 25 °C unless otherwise noted)

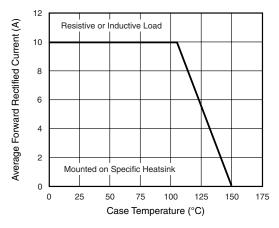


Figure 1. Forward Current Derating Curve

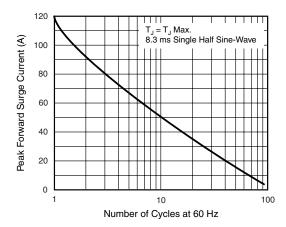


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode

⁽¹⁾ Pulse test: 300 µs pulse width, 1 % duty cycle



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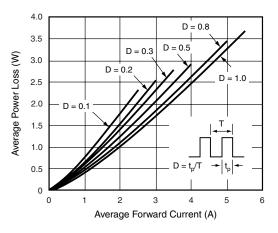


Figure 3. Forward Power Loss Characteristics Per Diode

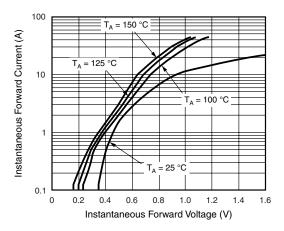


Figure 4. Typical Instantaneous Forward Characteristics Per Diode

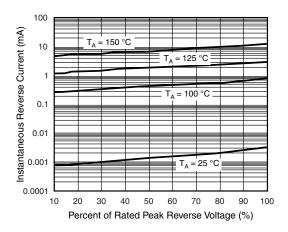


Figure 5. Typical Reverse Characteristics Per Diode

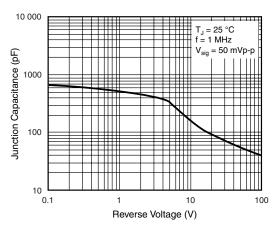


Figure 6. Typical Junction Capacitance Per Diode

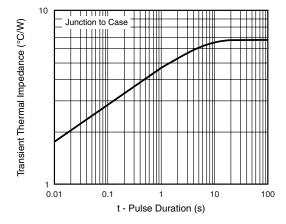
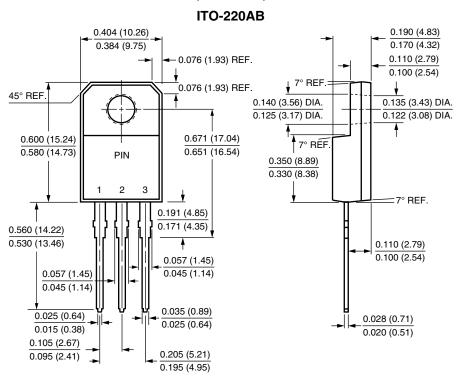


Figure 7. Typical Transient Thermal Impedance Per Diode

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PACKAGE OUTLINE DIMENSIONS in inches (millimeters)





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